



Picture serves as a representation only

Abstract

2N2169 is a bipolar Germanium PNP transistor used for high speed switching. The hermetically sealed TO-9 metal can package is highly durable and contributes to the longevity of the device. Through-hole mounting style.

Electrical Characteristics

	Value	Unit
Max I_{CBO}	3	μA
h_{FE}	40	min
@ I_C	10	mA
V_{CE}	0.5	V
f_T Min.	450	MHz
t_r Max.	18	nsec
t_f Max.	18	nsec
K'_s	50	nsec
C_{ob}	2.5	pF
$V_{CE} @ I_C=10mA$	0.15	V
$V_{BE} @ I_C=10mA$	0.36	V

Maximum Ratings

	Value	Unit
V_{CES}	15	V
V_{CEO}	15	V
$P_D @ 25^\circ C$	60	mW
I_C	100	mA

Package Style

TO-9 Metal Can

